



5N50

Preliminary

Power MOSFET

5A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

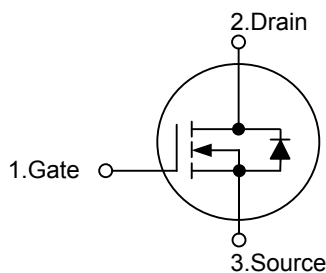
The UTC **5N50** is an N-channel power MOSFET adopting UTC's advanced technology to provide customers with DMOS, planar stripe technology. This technology is designed to meet the requirements of the minimum on-state resistance and perfect switching performance. It also can withstand high energy pulse in the avalanche and communication mode.

The UTC **5N50** can be used in applications, such as active power factor correction, high efficiency switched mode power supplies, electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} = 1.4\Omega @ V_{GS} = 10V$
- * 100% avalanche tested
- * High switching speed

SYMBOL

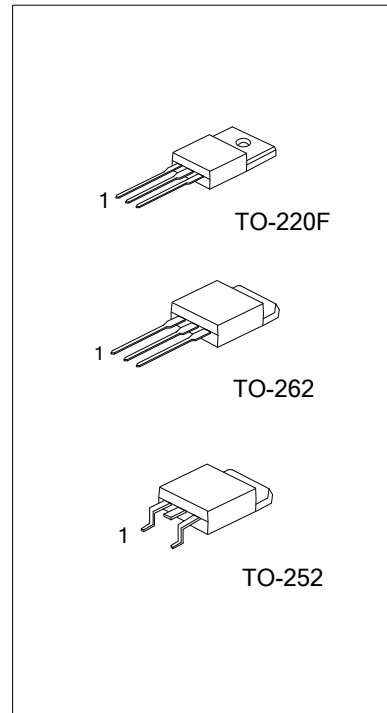


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
5N50L-TF3-T	5N50G-TF3-T	TO-220F	G	D	S	Tube
5N50L-TN3-R	5N50G-TN3-R	TO-252	G	D	S	Tape Reel
5N50L-T2Q-T	5N50G-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>5N50L-TN3-R</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Free</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TF3: TO-220F, TN3: TO-252, T2Q: TO-262</p> <p>(3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	5	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Current (Note 2)		I_{AR}	5	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	300	mJ
	Repetitive (Note 2)	E_{AR}	7.3	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F	P_D	38	W
	TO-252		54	W
	TO-262		125	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 21.5\text{mH}$, $I_{AS} = 5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	$^\circ\text{C}/\text{W}$
	TO-262		62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F	θ_{JC}	3.25	$^\circ\text{C}/\text{W}$
	TO-252		2.13	$^\circ\text{C}/\text{W}$
	TO-262		1	$^\circ\text{C}/\text{W}$

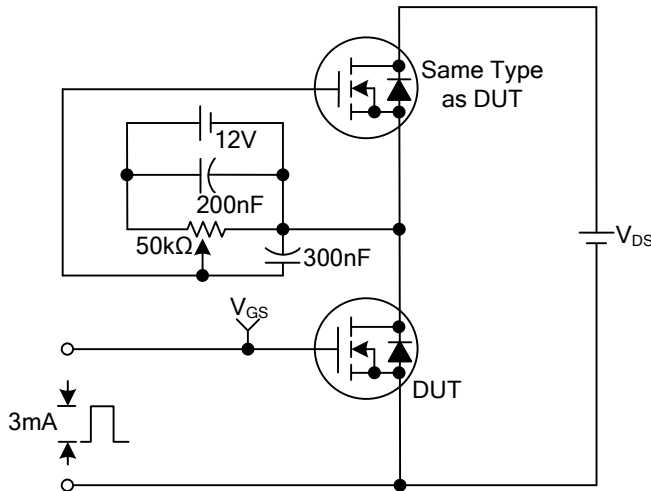
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=250\mu\text{A}$		0.5		$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$V_{DS}=400\text{V}$, $T_C=125^\circ\text{C}$			10	
Gate- Source Leakage Current	Forward	$V_{GS}=30\text{V}$, $V_{DS}=0\text{V}$			100	nA
	Reverse	$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=2.5\text{A}$		1.2	1.4	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		480	625	pF
Output Capacitance	C_{OSS}			80	105	pF
Reverse Transfer Capacitance	C_{RSS}			15	20	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=400\text{V}$, $I_D=5\text{A}$ (Note 1, 2)		18	24	nC
Gate to Source Charge	Q_{GS}			2.2		nC
Gate to Drain Charge	Q_{GD}			9.7		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250\text{V}$, $I_D=5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		12	35	ns
Rise Time	t_R			46	100	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			50	110	ns
Fall-Time	t_F			48	105	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				5	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				20	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=5\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Reverse Recovery Time	t_{rr}	$I_S=5\text{A}$, $V_{GS}=0\text{V}$,		263		ns
Reverse Recovery Charge	Q_{RR}	$dI_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		1.9		μC

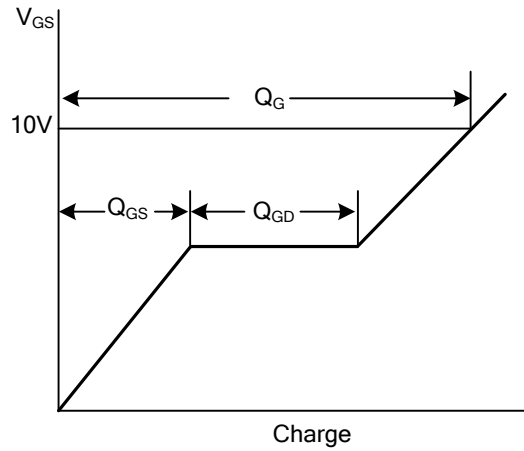
Note: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

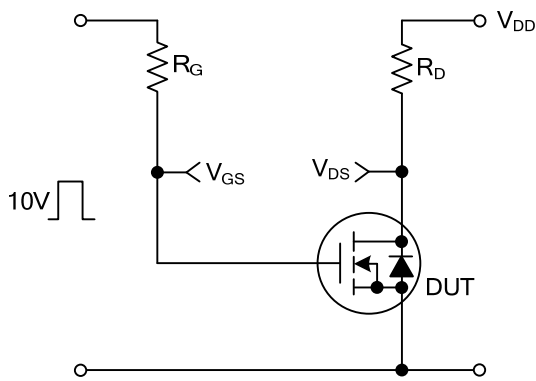
■ TEST CIRCUITS AND WAVEFORMS



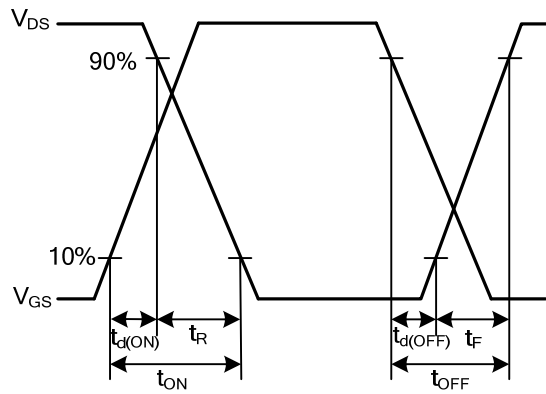
Gate Charge Test Circuit



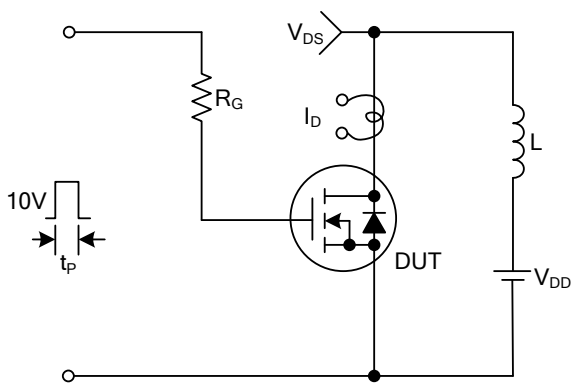
Gate Charge Waveforms



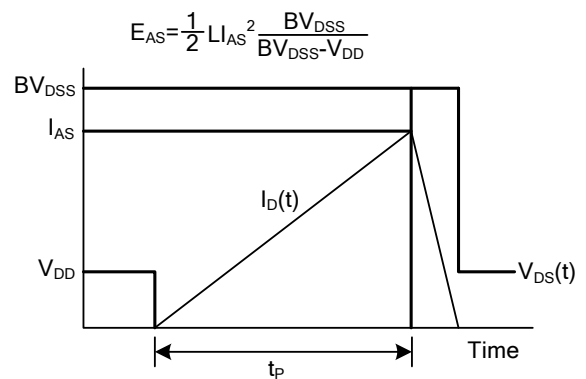
Resistive Switching Test Circuit



Resistive Switching Waveforms

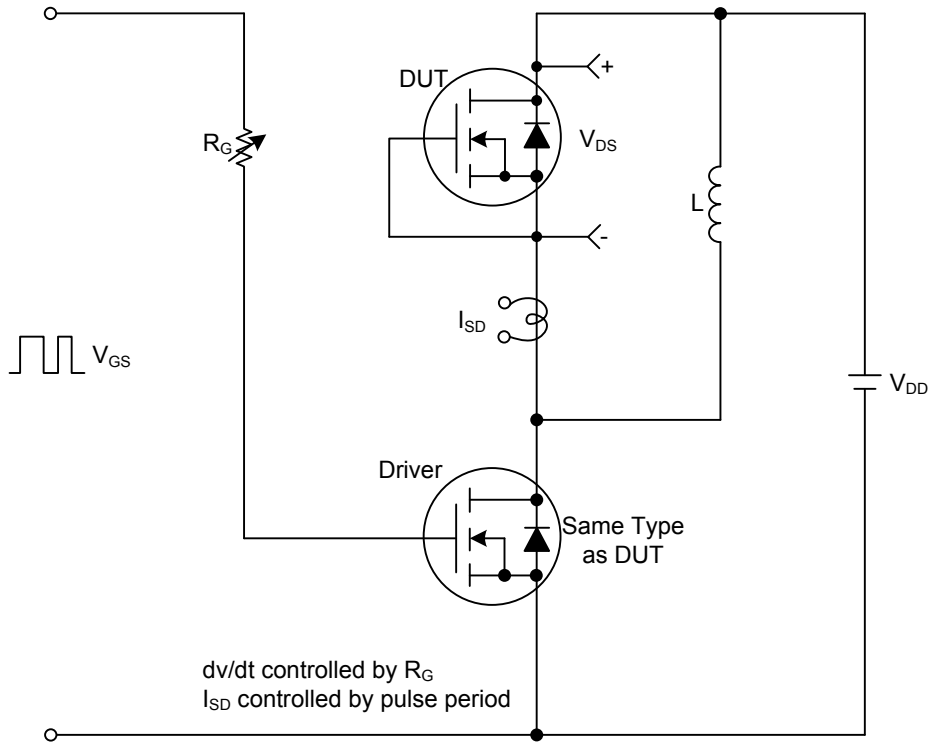


Unclamped Inductive Switching Test Circuit

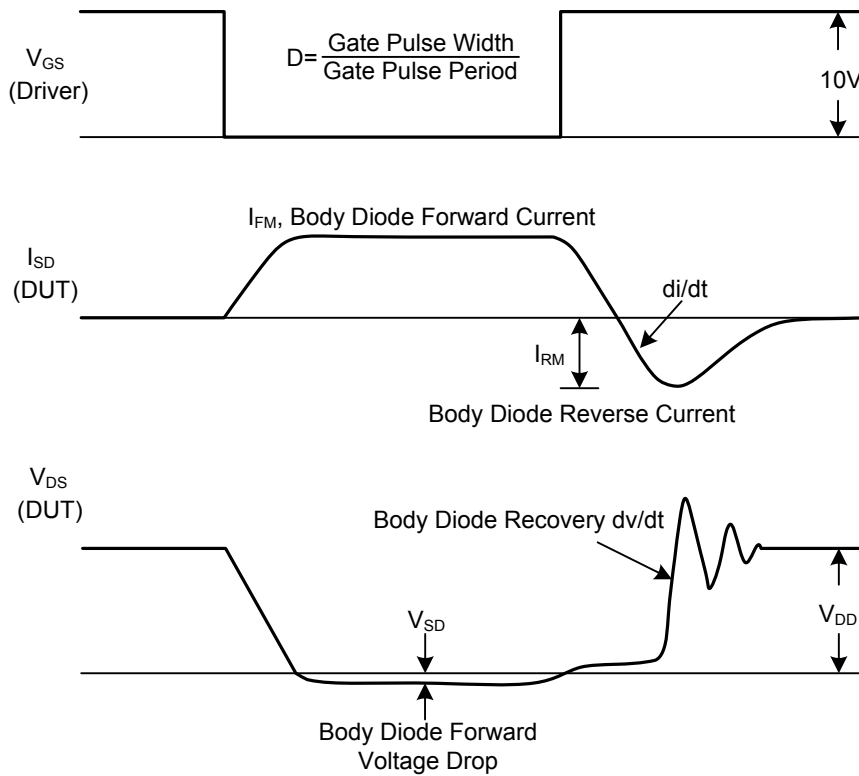


Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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